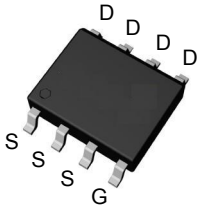
Features

- -30V/-7A,
  $R_{DS(ON)}$ = 30mΩ(typ.) @ V_{GS} =-10V
  $R_{DS(ON)}$ = 48mΩ(typ.) @ V_{GS} =-4.5V
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)
- HBM ESD protection level pass 2KV

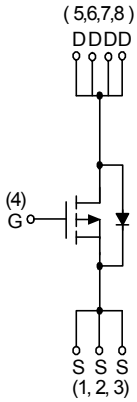
Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.
- Low Switch.

Pin Description



Top View of SOP8



P-Channel MOSFET

Absolute Maximum Ratings (T_A = 25°C Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
V_{DSS}	Drain-Source Voltage		-30	V
V_{GSS}	Gate-Source Voltage		±20	
I_D [a]	Continuous Drain Current (V_{GS}=-10V)	T_c=25°C	-7	A
		T_c=100°C	-5	
I_{DM} [a]	300μs Pulsed Drain Current (V_{GS}=-10V)		-21	
I_S [a]	Diode Continuous Forward Current		-7	
I_{AS} [b]	Avalanche Current, Single pulse	L=0.5mH	-9	
E_{AS} [b]	Avalanche Energy, Single pulse	L=0.5mH	20	mJ
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	
P_D [a]	Maximum Power Dissipation	T_A=25°C	2.8	W
		T_A=100°C	1.8	
$R_{\theta JA}$ [a]	Thermal Resistance-Junction to Ambient	t ≤ 10s	45	°C/W
		Steady State	85	
$R_{\theta JL}$	Thermal Resistance-Junction to Lead	Steady State	24	

Note a：Surface Mounted on 1in^2 pad area, t ≤ 10sec.
Note b：UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature T_j=25°C).

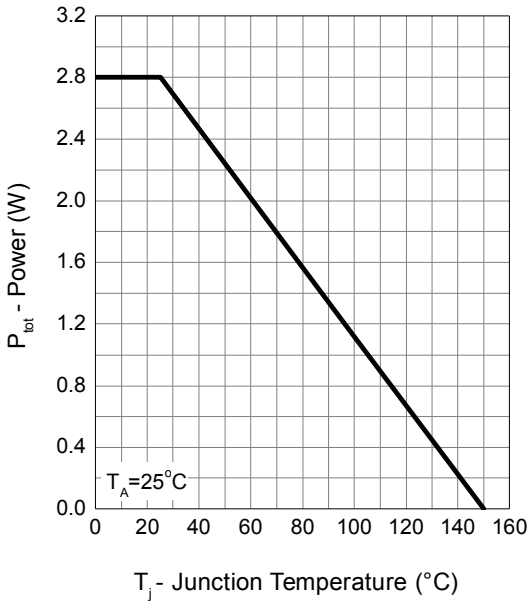
Electrical Characteristics (T_A = 25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=-250μA	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-24V, V_{GS}=0V	-	-	-1	μA
		T_J=85°C	-	-	-30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=-250μA	-1.0	-1.8	-2.5	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
$R_{DS(ON)}$ [c]	Drain-Source On-state Resistance	V_{GS}=-10V, I_{DS}=-8A	-	30	36	mΩ
		V_{GS}=-4.5V, I_{DS}=-5A	-	48	55	
Diode Characteristics						
V_{SD} [c]	Diode Forward Voltage	I_{SD}=-2A, V_{GS}=0V	-	-0.8	-1	V
t_{rr} [d]	Reverse Recovery Time	I_{SD}=-7A, di_{SD}/dt=100A/μs	-	18	-	ns
Q_{rr} [d]	Reverse Recovery Charge		-	10	-	nC
Dynamic Characteristics [d]						
R_g	Gate Resistance	V_{GS}=0V, V_{DS}=0V,F=1MHz	-	3.8	-	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-15V, Frequency=1.0MHz	-	638	-	pF
C_{oss}	Output Capacitance		-	115	-	
C_{rss}	Reverse Transfer Capacitance		-	88	-	
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=-15V, R_L=15Ω, I_{DS}=-1A, V_{GEN}=-10V, R_G=6Ω	-	9	-	ns
t_r	Turn-on Rise Time		-	11	-	
$t_{d(OFF)}$	Turn-off Delay Time		-	21	-	
t_f	Turn-off Fall Time		-	7	-	
Gate Charge Characteristics [d]						
Q_g	Total Gate Charge	V_{DS}=-15V, V_{GS}=-10V, I_{DS}=-7A	-	14.8	-	nC
Q_{gs}	Gate-Source Charge		-	1.1	-	
Q_{gd}	Gate-Drain Charge		-	4.4	-	

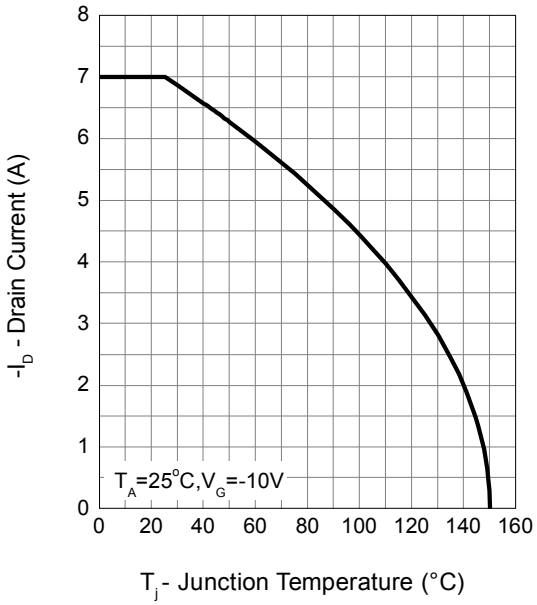
Note c：Pulse test ; pulse width≤300μs, duty cycle≤2%.
Note d：Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

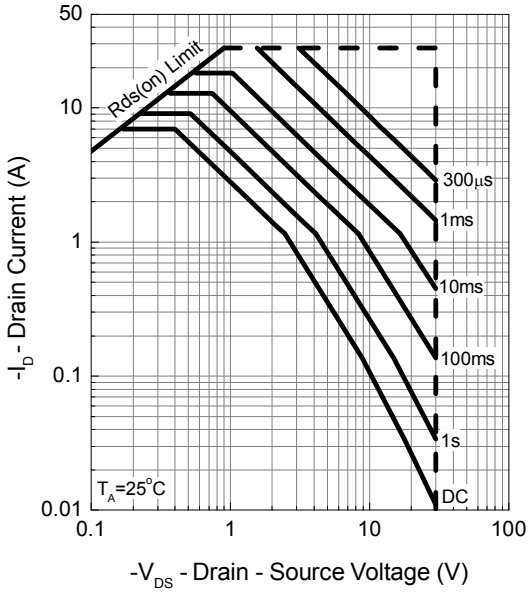
Power Dissipation



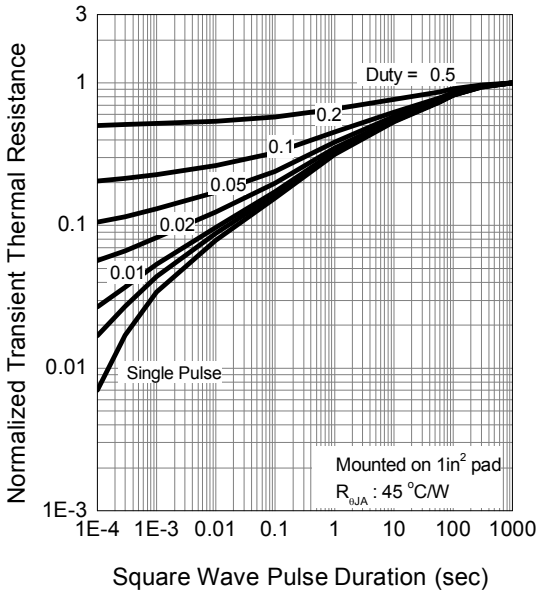
Drain Current



Safe Operation Area

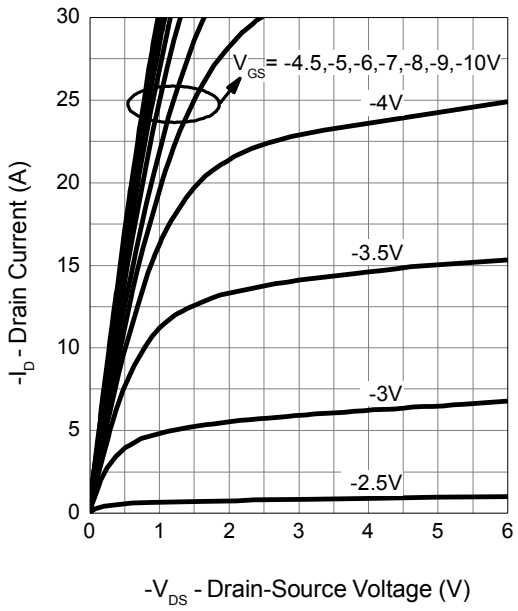


Thermal Transient Impedance

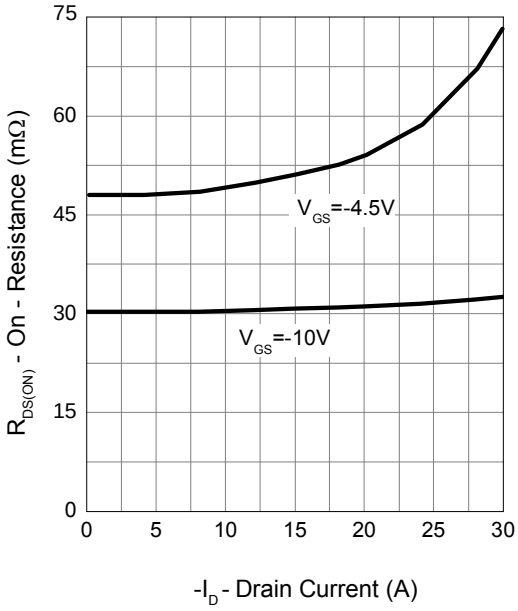


Typical Operating Characteristics (Cont.)

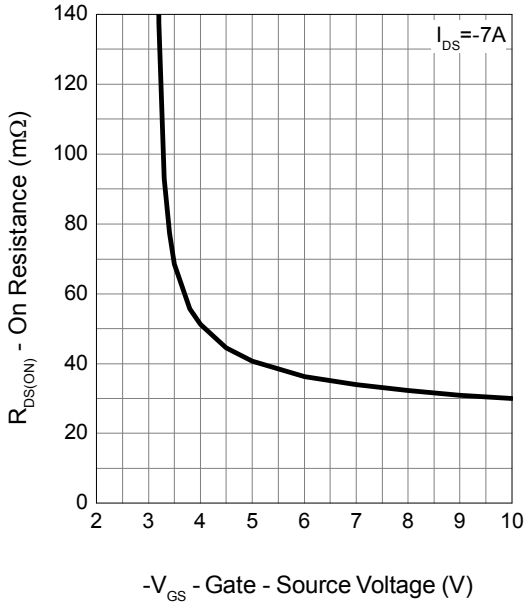
Output Characteristics



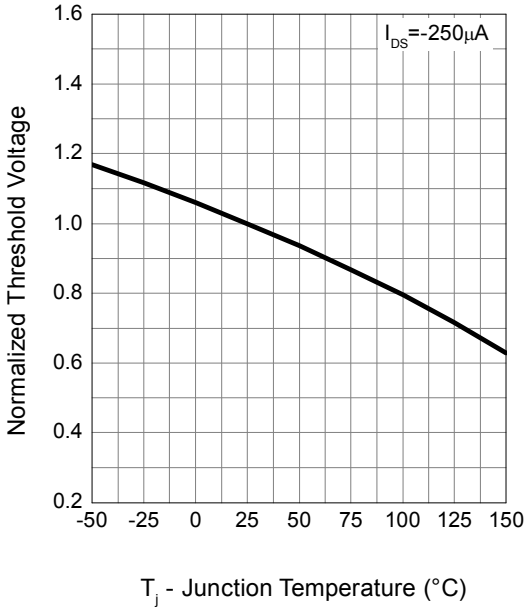
Drain-Source On Resistance



Gate-Source On Resistance

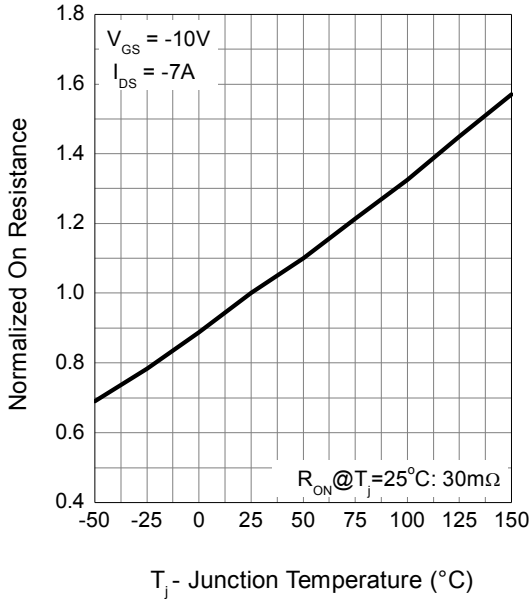


Gate Threshold Voltage

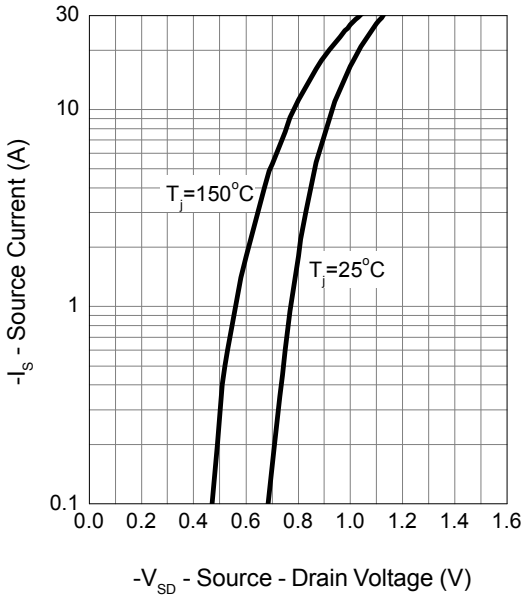


Typical Operating Characteristics (Cont.)

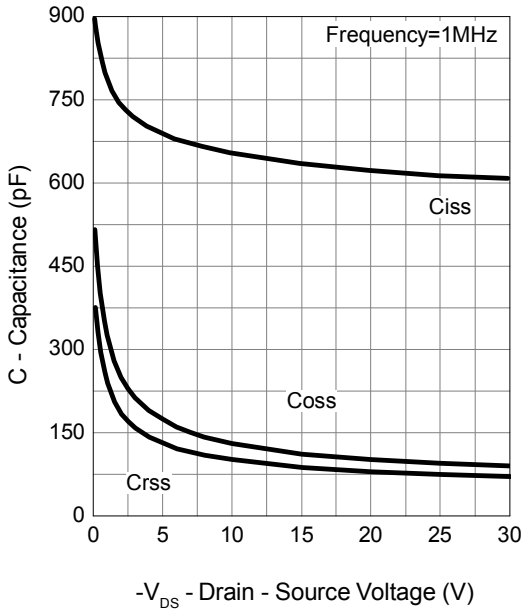
Drain-Source On Resistance



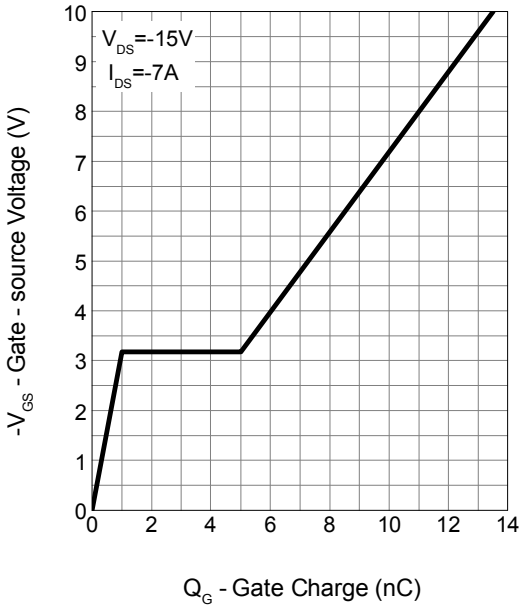
Source-Drain Diode Forward



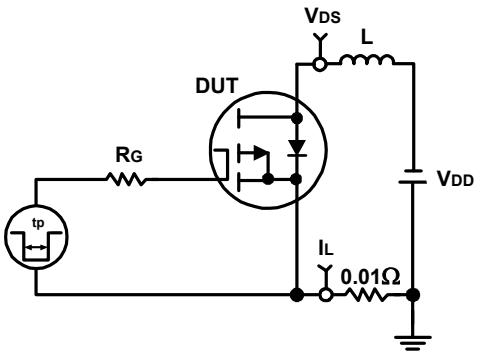
Capacitance

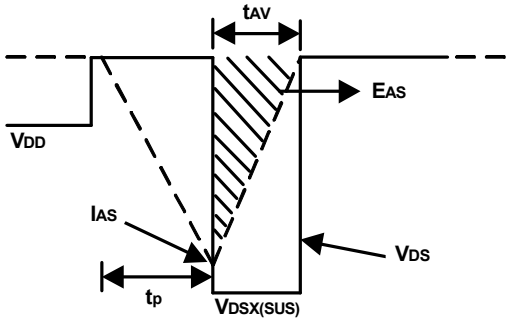


Gate Charge

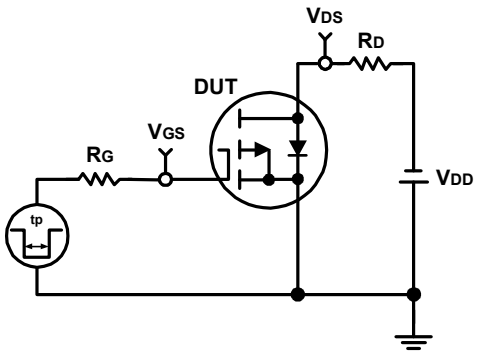


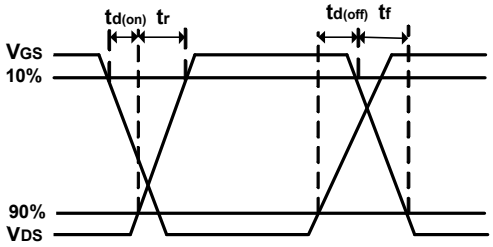
Avalanche Test Circuit and Waveforms





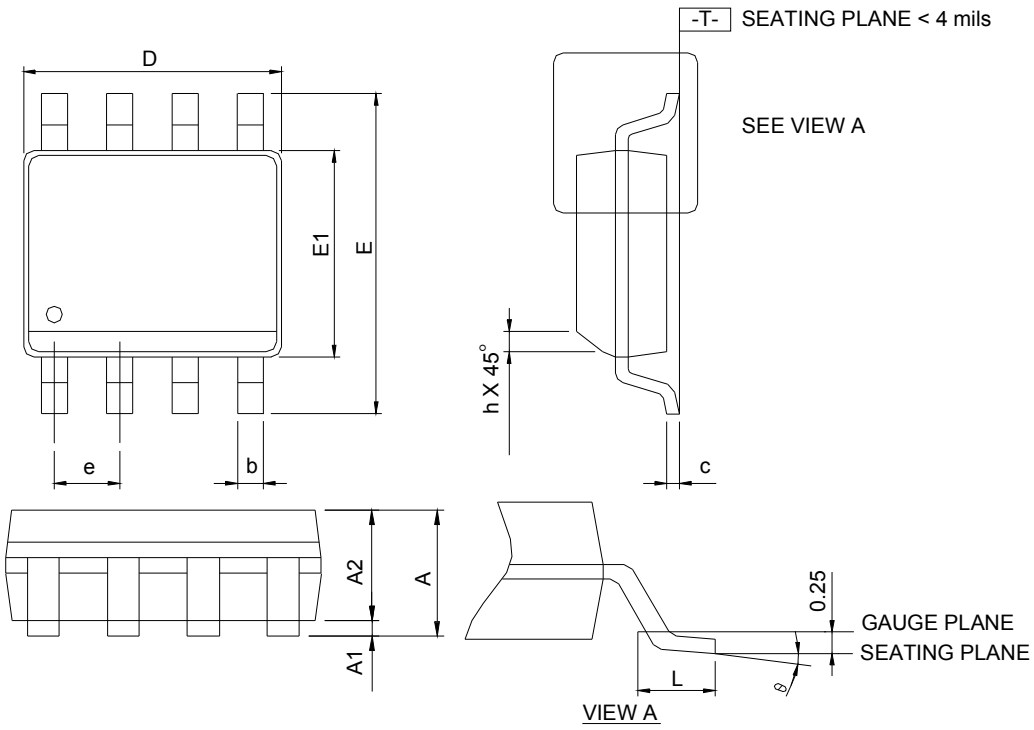
Switching Time Test Circuit and Waveforms





Package Information

SOP8



SYMBOL	SOP8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	-	1.75	-	0.069
A1	0.10	0.25	0.004	0.010
A2	1.25	-	0.049	-
b	0.31	0.51	0.012	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050
θ	0°	8°	0°	8°

Note: 1. Follow JEDEC MS-012 AA.
2. Dimension D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.
3. Dimension E" does not include inter-lead flash or protrusions. Inter-lead flash and protrusions shall not exceed 10 mil per side.

RECOMMENDED LAND PATTERN